# **DSC2002**

# Silicon NPN epitaxial planar type

For general amplification Complementary to DSA2002

### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- High forward current transfer ratio h<sub>FE</sub> with excellent linearity
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

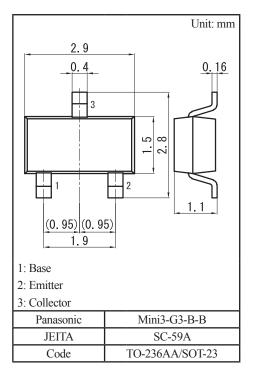
### ■ Marking Symbol: C2

#### ■ Packaging

DSC2002×0L Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

# ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub> 50		V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V	
Collector current	$I_{C}$	500	mA	
Peak collector current	$I_{CP}$	1	A	
Collector power dissipation	P <sub>C</sub>	200	mW	
Junction temperature	$T_j$	150	°C	
Operating ambient temperature	T <sub>opr</sub>	-40 to +85	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



## ■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	120		340	
	h <sub>FE2</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	40			_
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		0.1	0.6	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4.8	15	pF

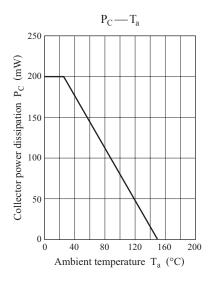
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

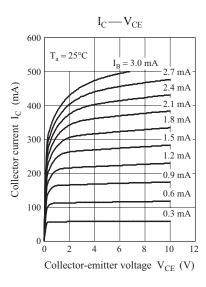
#### 2. \*1: Pulse measurement

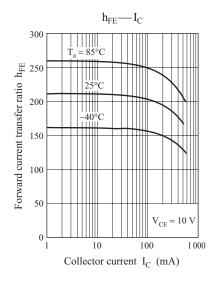
#### \*2: Rank classification

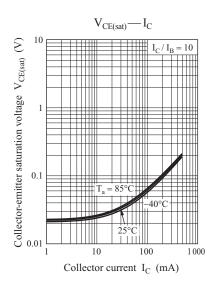
Code	R	S	0	
Rank	R	S	No-rank	
$h_{\mathrm{FE}}$	120 to 240	170 to 340	120 to 340	
Marking Symbol	C2R	C2S	C2	

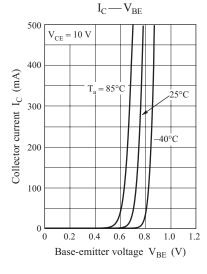
Product of no-rank is not classified and have no marking symbol for rank.

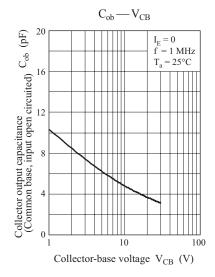


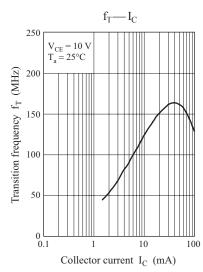








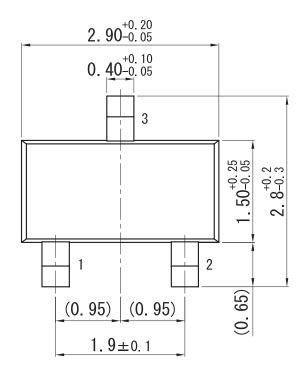


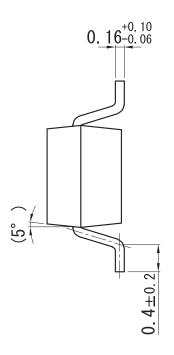


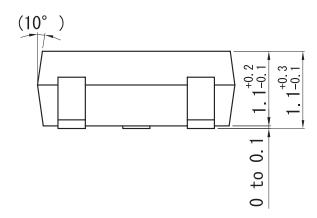
Ver. EED 2

Mini3-G3-B-B

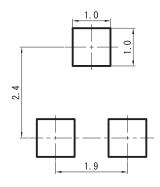
Unit: mm







# ■ Land Pattern (Reference) (Unit: mm)



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